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Vishay/Siliconix
SUM110N04-2M3L-E3

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SUM110N04-2m3L

Vishay Siliconix

N-Channel 40-V (D-S) 175 °C MOSFET

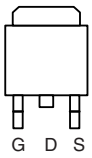
PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
40	0.0023 at V_{GS} = 10 V	110[a]
	0.003 at V_{GS} = 4.5 V	

FEATURES

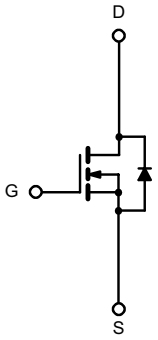
- TrenchFET® Power MOSFET
- 100 % R_g Tested

RoHS COMPLIANT

TO-263



Top View



N-Channel MOSFET

Ordering Information: SUM110N04-2m3L-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	110[a]	A
	T_C = 125 °C		110[a]	
Pulsed Drain Current		I_{DM}	440	
Avalanche Current, Single Pulse		I_{AS}	75	
Repetitive Avalanche Energy, Single Pulse	L = 0.1 mH	E_{AS}	280	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	375[b]	W
	T_A = 25 °C		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Typical**	**Unit**
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

Notes:
a. Package limited.
b. See SOA curve for voltage derating.
c. When Mounted on 1" square PCB (FR-4 material).

SUM110N04-2m3L

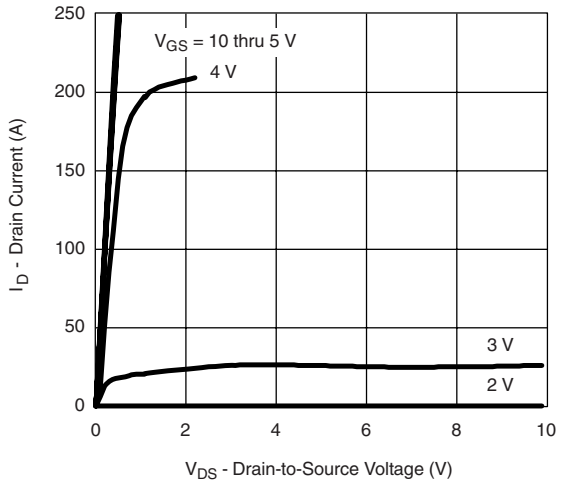
Vishay Siliconix

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			1	µA
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 175 °C			10	mA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A		0.0019	0.0023	Ω
		V_{GS} = 4.5 V, I_D = 20 A		0.0024	0.003	
		V_{GS} = 10 V, I_D = 30 A, T_J = 125 °C			0.0035	
		V_{GS} = 10 V, I_D = 30 A, T_J = 175 °C			0.0044	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	30			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		13600		pF
Output Capacitance	C_{oss}			1420		
Reverse Transfer Capacitance	C_{rss}			1040		
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 110 A		240	360	nC
Gate-Source Charge[c]	Q_{gs}			53		
Gate-Drain Charge[c]	Q_{gd}			55		
Gate Resistance	R_g	f = 1.0 MHz	0.65	1.3	2	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.27 Ω I_D ≅ 110 A, V_{GEN} = 10 V, R_g = 2.5 Ω		25	40	ns
Rise Time[c]	t_r			100	150	
Turn-Off Delay Time[c]	$t_{d(off)}$			125	190	
Fall Time[c]	t_f			200	300	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				110	A
Pulsed Current	I_{SM}				240	
Forward Voltage[a]	V_{SD}	I_F = 85 A, V_{GS} = 0 V		1.1	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 85 A, di/dt = 100 A/µs		56	85	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$			3.1	4.7	A
Reverse Recovery Charge	Q_{rr}			0.087	0.2	µC

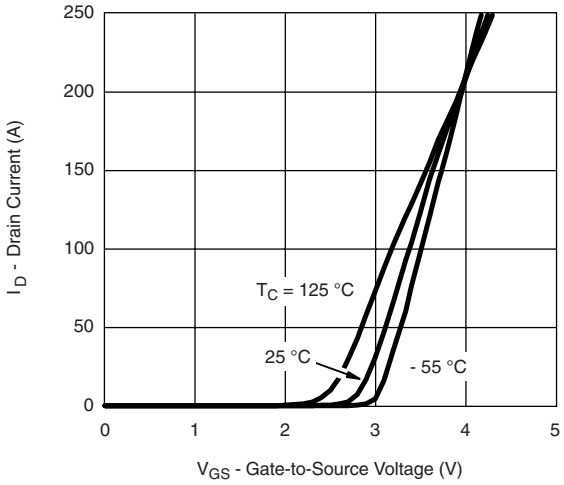
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

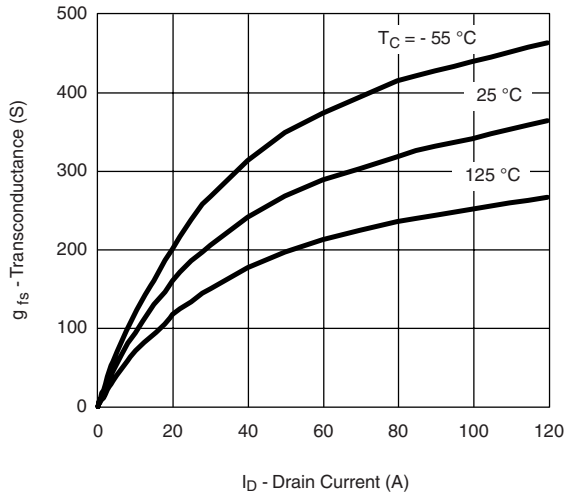
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



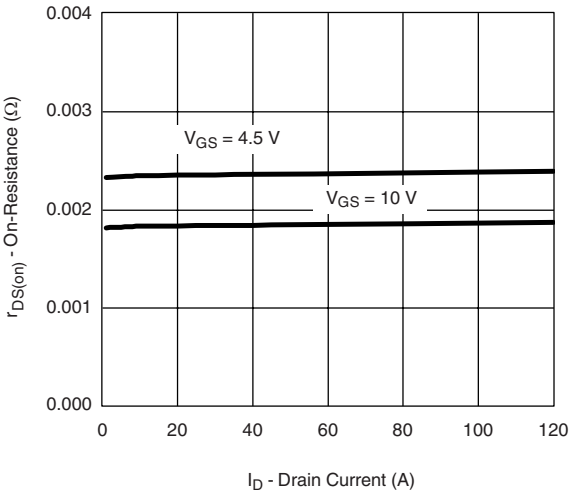
Output Characteristics



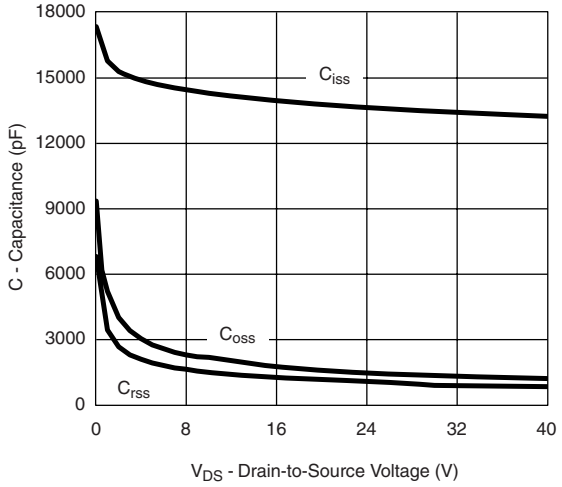
Transfer Characteristics



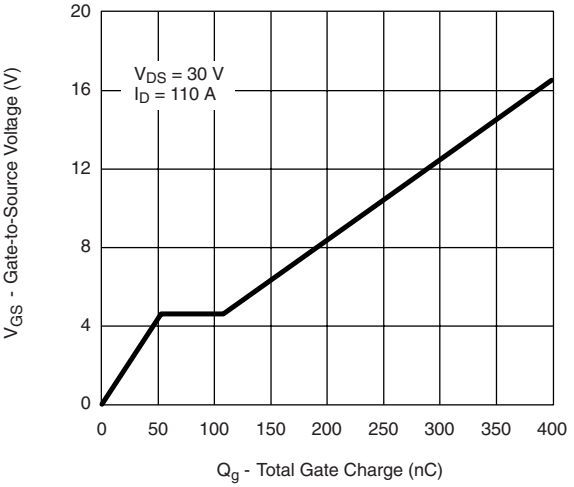
Transconductance



On-Resistance vs. Drain Current

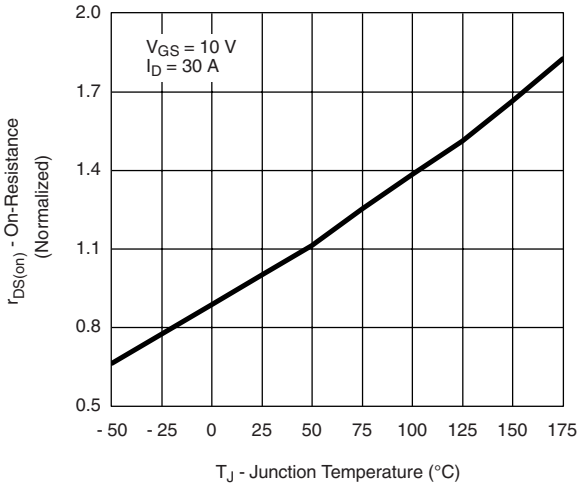


Capacitance

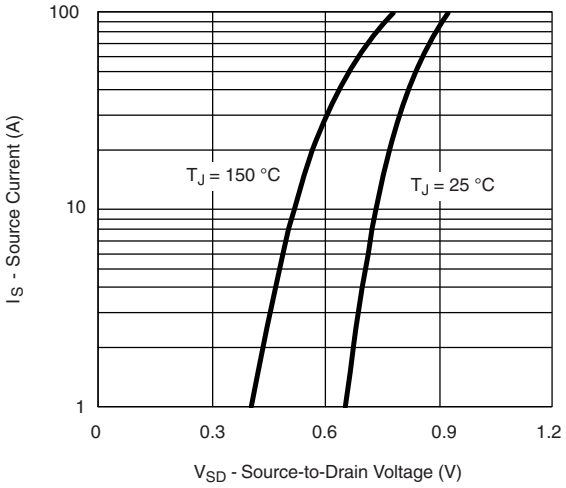


Gate Charge

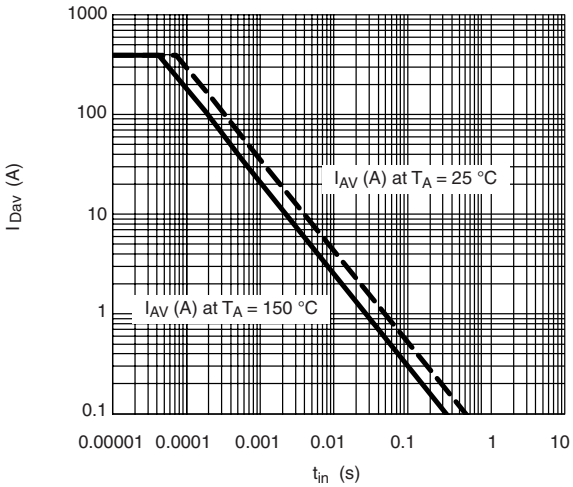
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



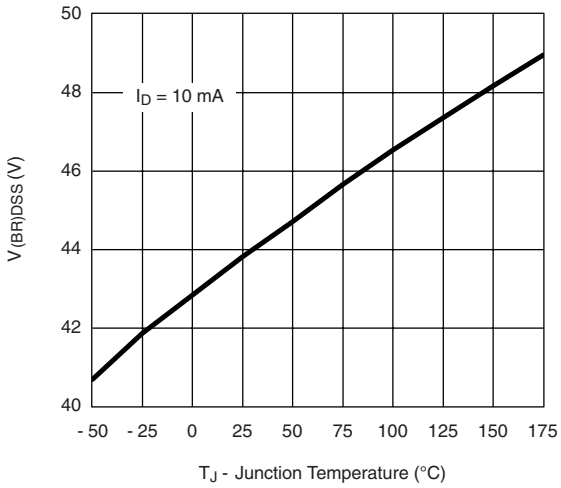
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

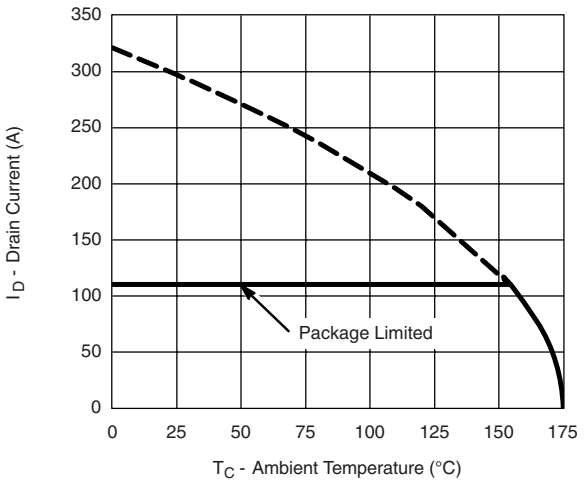


Avalanche Current vs. Time

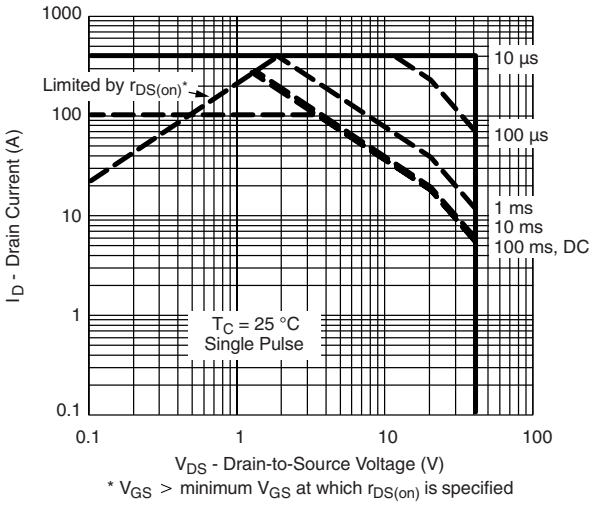


Drain Source Breakdown vs. Junction Temperature

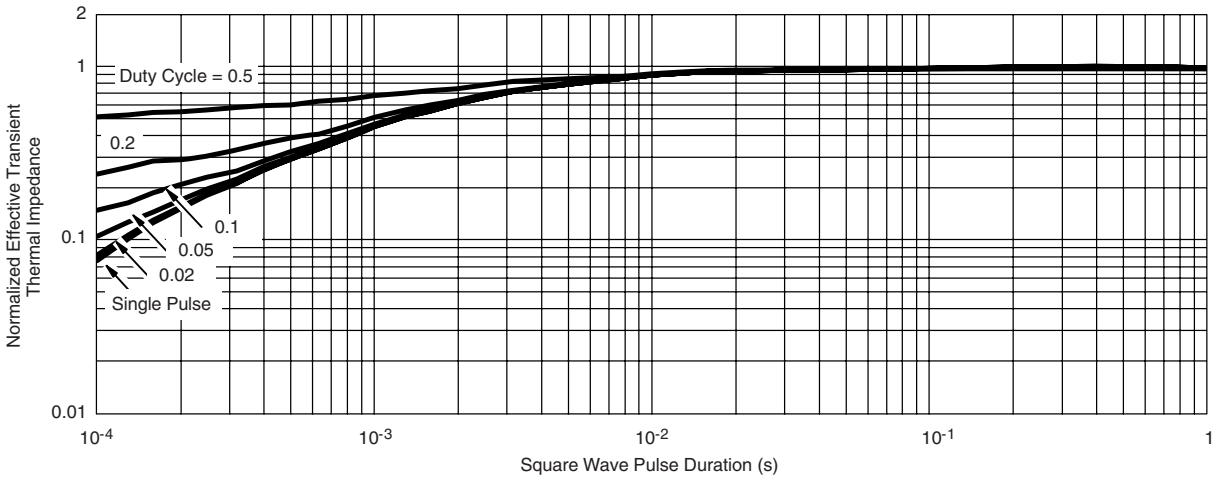
THERMAL RATINGS



Maximum Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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